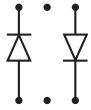


CMKD6263DO

SURFACE MOUNT
DUAL OPPOSING
HIGH VOLTAGE SILICON
SCHOTTKY DIODES

ULTRAmTM



SOT-363 CASE

Central
Semiconductor Corp.

www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6263DO contains two (2) galvanically isolated, high voltage, low V_F Silicon Schottky diodes with an opposing Anode/Cathode configuration, epoxy molded in a SOT-363 surface mount package. This ULTRAmTM device has been designed for fast switching applications requiring a low forward voltage drop.

MARKING CODE: 63D

FEATURES:

- Dual Opposing (DO) Schottky Diodes
- Low Forward Voltage
- High Voltage (70V)
- Galvanically Isolated

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Peak Repetitive Reverse Voltage
Continuous Forward Current
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{RRM} 70
 I_F 15
 I_{FSM} 50
 P_D 250
 T_J, T_{stg} -65 to +150
 θ_{JA} 500

UNITS

V
mA
mA
mW
 $^\circ\text{C}$
 $^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

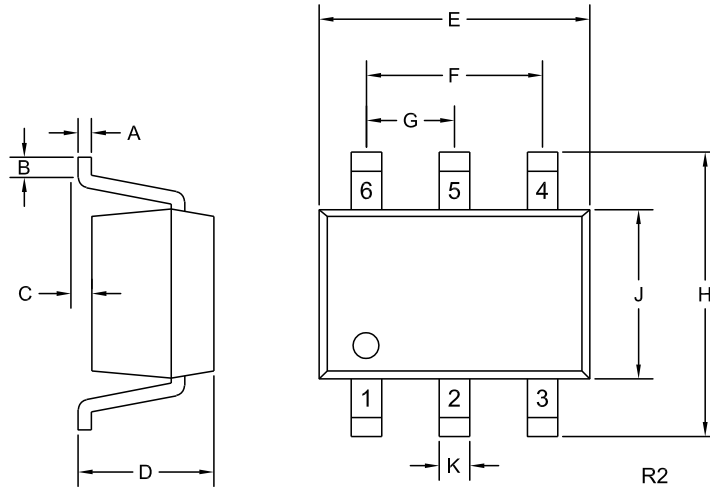
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=50\text{V}$		98	200	nA
BV_R	$I_R=10\mu\text{A}$	70			V
V_F	$I_F=1.0\text{mA}$		395	410	mV
C_T	$V_R=0, f=1.0\text{MHz}$			2.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R3 (13-January 2010)

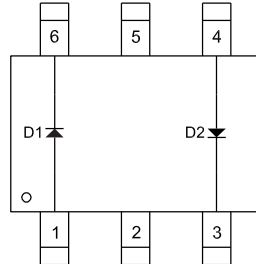
CMKD6263DO
SURFACE MOUNT
DUAL OPPOSING
HIGH VOLTAGE SILICON
SCHOTTKY DIODES



SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
- 2) NC
- 3) Cathode D2
- 4) Anode D2
- 5) NC
- 6) Cathode D1

MARKING CODE: 63D

DIMENSIONS

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

R3 (13-January 2010)